

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13861	differential with power with amplif\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:20
L2	3873	capacitor with drain with FET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:20
L3	9535	capacitor with gate with (FET (field near2 effect near2 transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:20
L4	61916	((field near2 effect near2 transistor) FET) with source with ((field near2 effect near2 transistor) FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:20
L5	1286	induct\$3 with source with ((field near2 effect near2 transistor) FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:20
L6	4	L1 and L2 and L3 and L4 and L5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:26
L7	61474	"333"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:27
L8	518	(FBAR or film near2 bulk near2 acoutic\$1 near2 resonator\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/06 13:27

L9	139	7 and L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:27
L10	10652	duplexer\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/06 13:27
L11	68	7 and L8 and L10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:27
L12	26	7 and (L8 with L10)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:31
L13	801	333/189.ccls. or 333/133.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:32
L14	17	L13 and (L8 with L10)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:32
S1	1	("6472954").PN.	USPAT; USOCR	OR	OFF	2005/06/06 13:19
S2	512	(FBAR or film near2 bulk near2 acoustic\$1 near2 resonator\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/03 11:27
S3	20	differential\$1 near3 duplexer\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/03 11:34

S4	4	S2 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/03 11:27
S5	10641	duplexer\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/03 11:34
S6	144	S2 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/03 11:34
S7	62	S2 with S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/03 11:34
S8	42	((field near2 effect near2 transistor) FET) with gate with ((IMN) (input\$4 near3 match\$3 near3 network\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:06
S9	3873	capacitor with drain with FET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:07
S10	11	S8 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:07
S11	9535	capacitor with gate with (FET (field near2 effect near2 transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:08

S12	8	S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:09
S13	61916	((field near2 effect near2 transistor) FET) with source with ((field near2 effect near2 transistor) FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:10
S14	8	S12 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:10
S15	1286	induct\$3 with source with ((field near2 effect near2 transistor) FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:11
S16	2	S14 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 13:11